

## N-Channel Power MOSFET

800V, 5.5A, 1.2Ω

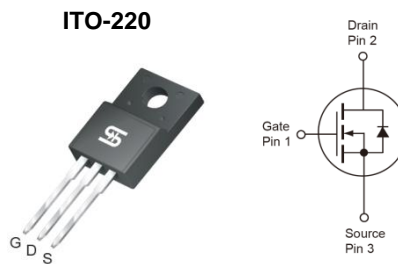
### FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
$V_{DS}$	800	V
$R_{DS(on)}$ (max)	1.2	Ω
$Q_g$	19.4	nC

### APPLICATIONS

- Power Supply
- Lighting



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	800	V
Gate-Source Voltage	$V_{GS}$	±30	V
Continuous Drain Current <sup>(Note 1)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	5.5
		$T_C = 100^\circ\text{C}$	3.4
Pulsed Drain Current <sup>(Note 2)</sup>	$I_{DM}$	16.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_{DTOT}$	25	W
Single Pulse Avalanche Energy <sup>(Note 3)</sup>	$E_{AS}$	121	mJ
Single Pulse Avalanche Current <sup>(Note 3)</sup>	$I_{AS}$	2.2	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	°C

**THERMAL PERFORMANCE**

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	5	$^{\circ}\text{C}/\text{W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

**Notes:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

**ELECTRICAL SPECIFICATIONS** ( $T_A = 25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	$BV_{DSS}$	800	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2	--	4	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 800\text{V}, V_{GS} = 0\text{V}$	$I_{DSS}$	--	--	1	$\mu\text{A}$
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10\text{V}, I_D = 1.8\text{A}$	$R_{DS(on)}$	--	0.9	1.2	$\Omega$
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$V_{DS} = 380\text{V}, I_D = 5.5\text{A}, V_{GS} = 10\text{V}$	$Q_g$	--	19.4	--	nC
Gate-Source Charge		$Q_{gs}$	--	3.4	--	
Gate-Drain Charge		$Q_{gd}$	--	9.6	--	
Input Capacitance	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	$C_{iss}$	--	685	--	pF
Output Capacitance		$C_{oss}$	--	62	--	
Gate Resistance	$F = 1\text{MHz}, \text{open drain}$	$R_g$	--	3.4	--	$\Omega$
<b>Switching</b> (Note 6)						
Turn-On Delay Time	$V_{DD} = 380\text{V}, R_{GEN} = 25\Omega, I_D = 5.5\text{A}, V_{GS} = 10\text{V},$	$t_{d(on)}$	--	22	--	ns
Turn-On Rise Time		$t_r$	--	11	--	
Turn-Off Delay Time		$t_{d(off)}$	--	55	--	
Turn-Off Fall Time		$t_f$	--	10	--	
<b>Source-Drain Diode</b>						
Forward On Voltage (Note 4)	$I_S = 5.5\text{A}, V_{GS} = 0\text{V}$	$V_{SD}$	--	--	1.4	V
Reverse Recovery Time	$V_R = 100\text{V}, I_S = 5.5\text{A}$	$t_{rr}$	--	240	--	ns
Reverse Recovery Charge		$dI_F/dt = 100\text{A}/\mu\text{s}$	$Q_{rr}$	--	2.5	--

**Notes:**

- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- $L = 50\text{mH}, I_{AS} = 2.2\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega,$  Starting  $T_J = 25^{\circ}\text{C}$
- Pulse test:  $PW \leq 300\mu\text{s}, \text{duty cycle} \leq 2\%$ .
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

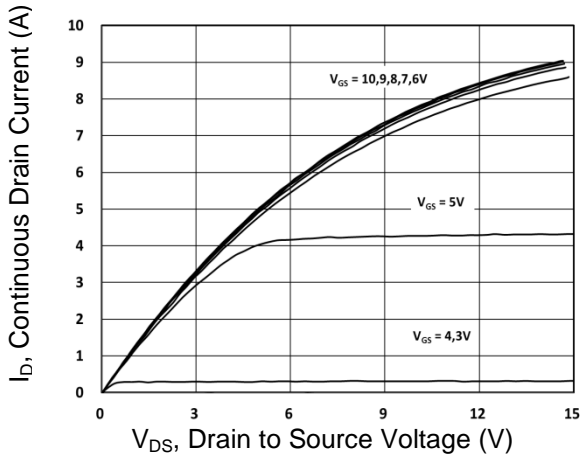
**ORDERING INFORMATION**

<b>PART NO.</b>	<b>PACKAGE</b>	<b>PACKING</b>
TSM80N1R2CI C0G	ITO-220	50pcs / Tube

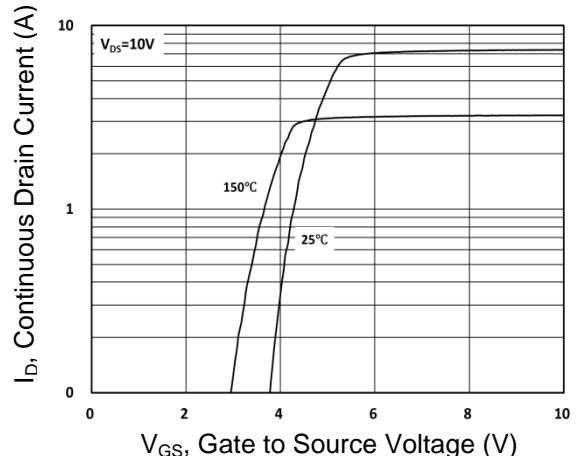
**CHARACTERISTICS CURVES**

( $T_c = 25^\circ\text{C}$  unless otherwise noted)

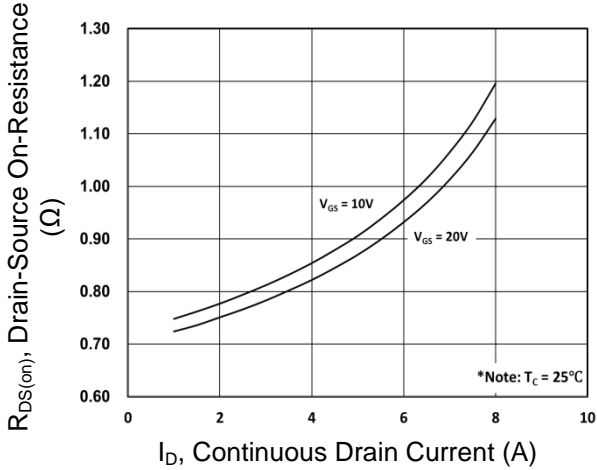
**Output Characteristics**



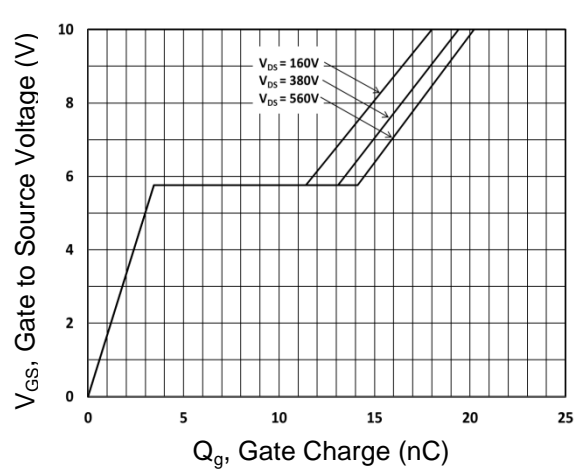
**Transfer Characteristics**



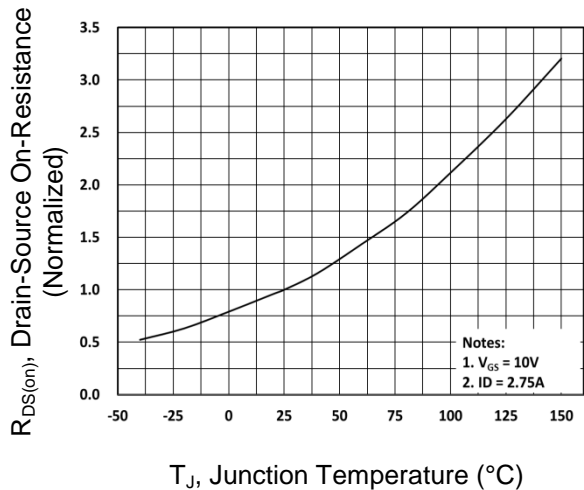
**On-Resistance vs. Drain Current**



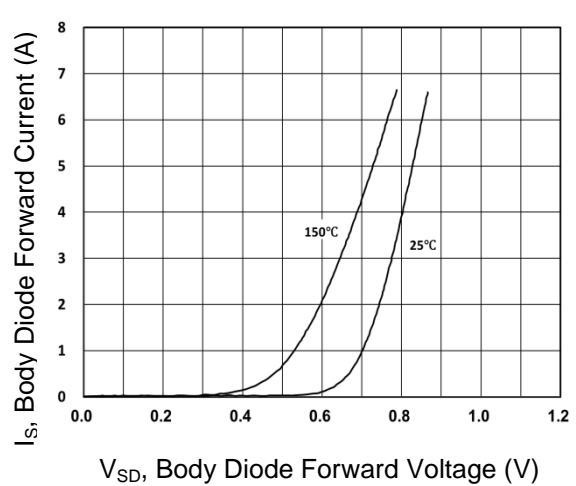
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



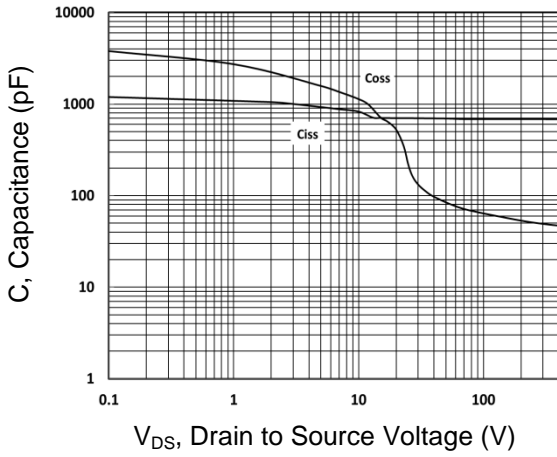
**Source-Drain Diode Forward Current vs. Voltage**



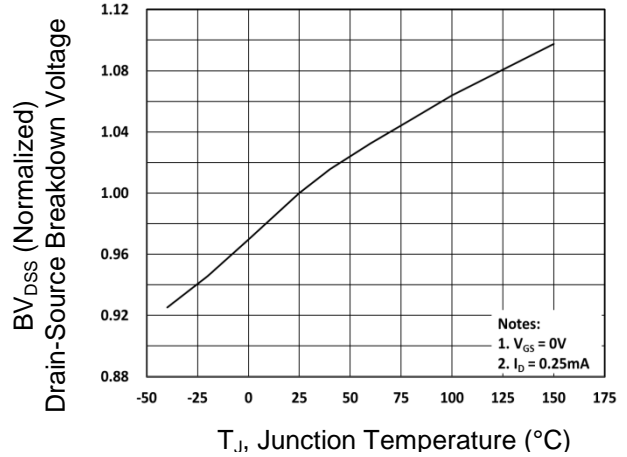
**CHARACTERISTICS CURVES**

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

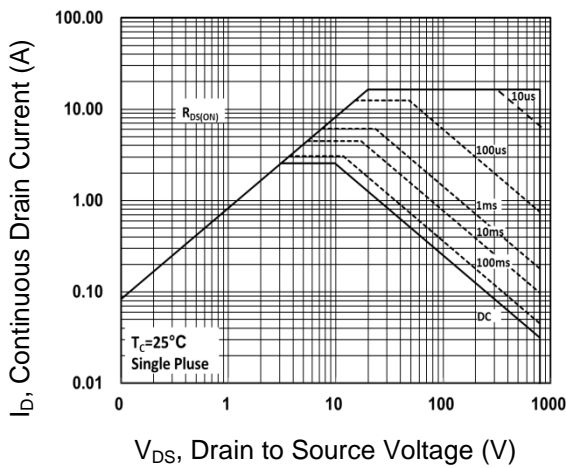
**Capacitance vs. Drain-Source Voltage**



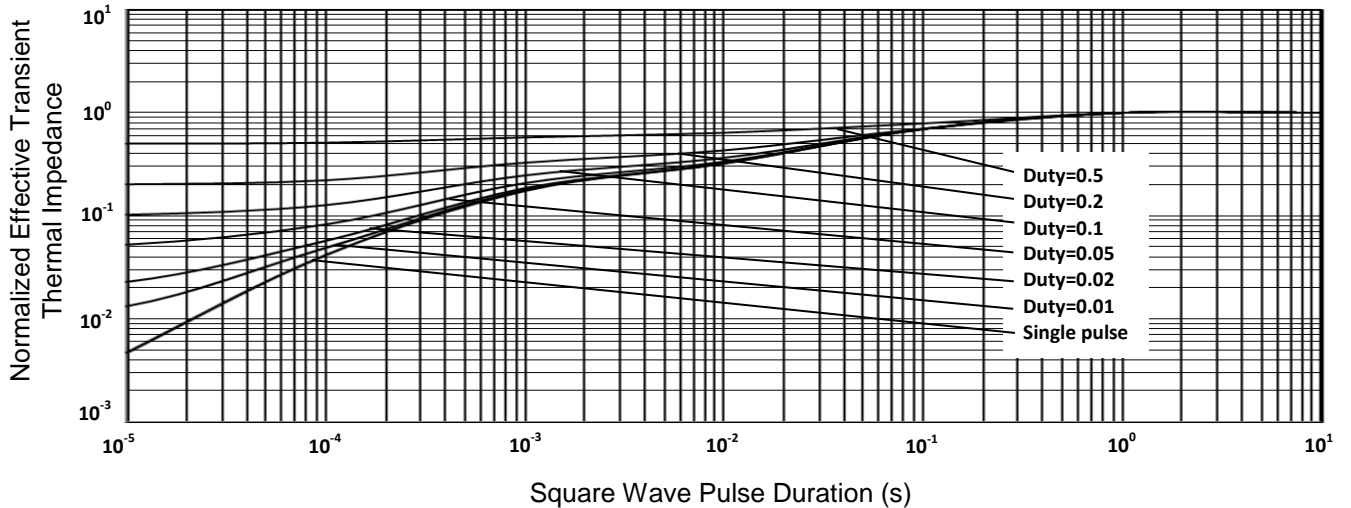
**$BV_{DSS}$  vs. Junction Temperature**



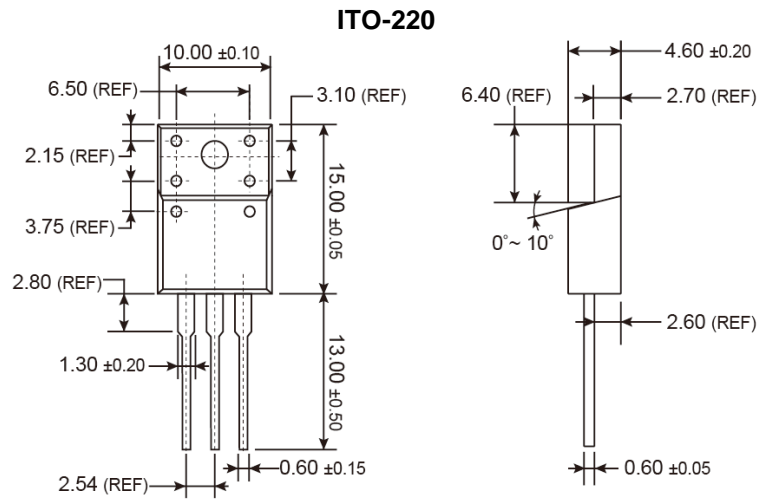
**Maximum Safe Operating Area**



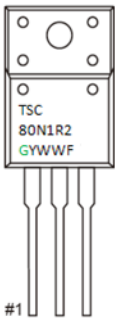
**Normalized Thermal Transient Impedance, Junction-to-Case**



**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)



**MARKING DIAGRAM**



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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